



100V DUAL NPN LOW SAT TRANSISTORS IN PowerDI5060-8

Features

- BV_{CEO} > 100V
- I_C = 3A Continuous Collector Current
- I_{CM} = 8A Peak Pulse Current
- $R_{CE(sat)} = 90m\Omega (Typ)$
- Complementary Part DXTP3C100PDQ
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DXTN3C100PDQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: PowerDI5060-8/SWP (Type UXD)
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Lead-Frame;
 Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)

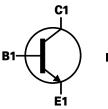
Applications

- Power Management
- Motor Drive
- Linear Mode Voltage Regulators
- Backlighting Applications

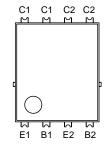












Top View Pin Configuration

Ordering Information (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
DXTN3C100PDQ-13	Automotive	DXTN3C100PD	13	12	2,500

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information

PowerDI5060-8/SWP (Type UXD)



DXTN3 = Product Type Marking Code C100PD = Product Type Marking Code \overline{\text{YYWW}} = Date Code Marking \overline{\text{YY}} = Last Digit of Year (ex: 21 = 2021) WW = Week Code (01 to 53)



Absolute Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	100	V
Collector-Emitter Voltage	V _{CEO}	100	V
Emitter-Base Voltage	V _{EBO}	7	V
Base Current	I _B	500	mA
Continuous Collector Current	Ic	3	А
Peak Pulse Collector Current	I _{CM}	8	А

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	r Dissipation (Notes 5, 7)		1.47	W	
Linear Derating Factor	(Notes 6, 7)	P _D	11.76	mW/°C	
Thermal Desigtance, Junction to Ambient	(Notes 5, 7)	0	85	°C/W	
Thermal Resistance, Junction to Ambient	(Notes 6, 7)	$R_{\theta JA}$	37		
Thermal Resistance, Junction to Lead	(Note 8)	$R_{ heta JL}$	5.7		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge – Charged Device Model	ESD CDM	1000	V	C3

Notes:

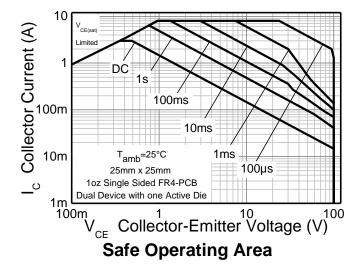
- 5. For a device mounted with the collector lead on 25mm x 25mm 1oz copper that is on single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

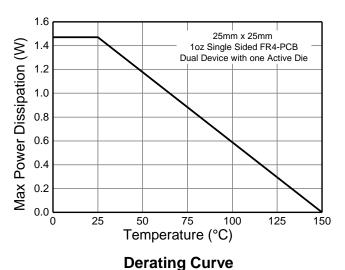
 6. Same as Note 5, except the device is measured at t ≤ 5 sec.

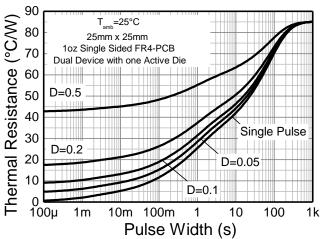
- Saline as invited, except the device is measured at 1 ≤ 3 sec.
 For a dual device with one active die.
 Thermal resistance from junction to solder-point (at the end of the collector lead).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.

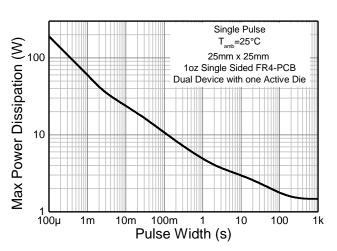


Thermal Characteristics and Derating Information









Transient Thermal Impedance

Pulse Power Dissipation



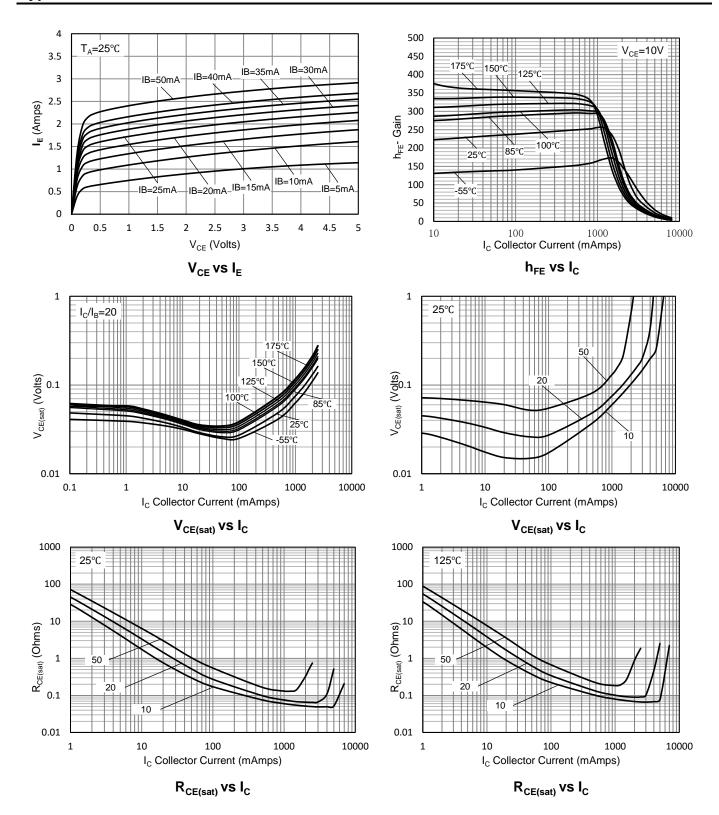
Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	100	_	_	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	100	_	_	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	_	_	٧	I _E = 100μA
Collector-Base Cutoff Current		_	_	100	nA	V _{CB} = 80V
Conector-base Cuton Current	I _{CBO}	_	_	50	μΑ	V _{CB} = 80V @Tj = 150°C
Emitter Cutoff Current	I _{EBO}	_	_	100	nA	V _{EB} = 7V
Collector-Emitter Cutoff Current	I _{CES}	_	_	100	nA	V _{CES} = 80V
ON CHARACTERISTICS (Note 10)						
		150	250	_		$I_C = 500 \text{mA}, V_{CE} = 10 \text{V}$
DC Current Gain	h	80	250	_	_	$I_C = 1A, V_{CE} = 10V$
De current dani	h _{FE}	20	100	_		$I_C = 2A, V_{CE} = 10V$
		10	40	_		$I_C = 3A$, $V_{CE} = 10V$
Collector-Emitter Saturation Voltage	V	_	90	150	mV	$I_C = 1A, I_B = 50mA$
Conector-Emitter Saturation Voltage	V _{CE(sat)}	_	225	330	mV	$I_C = 3A, I_B = 300mA$
Collector-Emitter Saturation Resistance	R _{CE(sat)}	_	90	150	mΩ	$I_C = 1A, I_B = 50mA$
Base-Emitter Saturation Voltage	V _{BE(sat)}	_	0.86	1.0	V	$I_C = 1A, I_B = 50mA$
base-Emilier Galdrallon Vollage		_	1.0	1.2	V	$I_C = 2A$, $I_B = 200mA$
Base-Emitter Turn-On Voltage	V _{BE(on)}	_	0.67	0.85	V	$I_C = 0.1A, V_{CE} = 2V$
SMALL SIGNAL CHARACTERISTICS						
Current Gain-Bandwidth Product	f⊤	_	130	_	MHz	V _{CE} = 10V, I _C = 100mA, f = 100MHz
Output Capacitance	C _{obo}		11	_	pF	V _{CB} = 10V, f = 1MHz
Delay Time	t _d		40	_	ns	
Rise Time	tr	_	20	_	ns	
Turn-On Time	t _(on)	_	60	_	ns	V _{CC} = 12.5V, I _C = 1A
Storage Time	ts	_	620	_	ns	$I_{B1} = -I_{B2} = 0.05A$
Fall Time	t _f		40	_	ns	
Turn-Off Time	t _{off}	_	660	_	ns	

Note: 10. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2\%$.

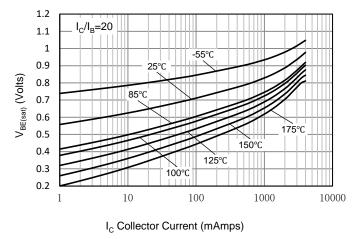


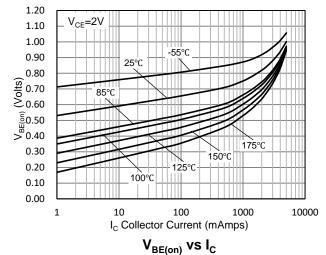
Typical Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)





Typical Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.) (continued)



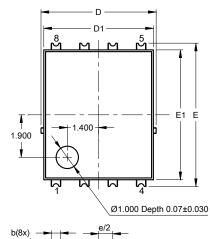


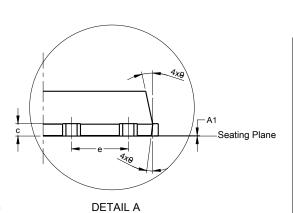


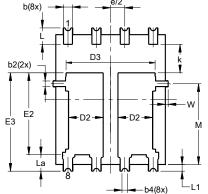
Package Outline Dimensions

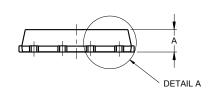
Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8/SWP (Type UXD)







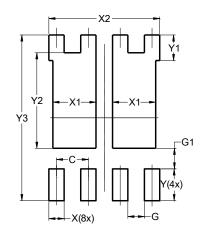


PowerDI5060-8/SWP					
(Type UXD)					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05			
b	0.30	0.50	0.41		
b2	0.20	0.35	0.25		
b4	().25REF			
С	0.230	0.330	0.277		
D	5	.15 BS0			
D1	4.70	5.10	4.90		
D2	1.46	1.66	1.55		
D3	3.78	4.18	3.98		
Е	6.40 BSC				
E1	5.60	6.00	5.80		
E2	3.46	3.86	3.66		
E2a	4.195	4.595	4.395		
е	1	.27BSC)		
k	1.05				
L	0.635	0.835	0.735		
La	0.635	0.835	0.735		
L1	0.200	0.400	0.300		
М	3.205	4.005	3.605		
W	0.025	0.225	0.125		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8/SWP (Type UXD)



Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
Х	0.610		
X1	1.720		
X2	4.420		
Υ	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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